

## 28th RD50 Workshop (Torino)



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## Characterization of NitroSil diodes at KIT

Diodes made from three different wafer materials (FZ, N-rich FZ, O-rich FZ) have been irradiated with protons ( $5e13$  to  $5e15$  neq/cm<sup>2</sup>) and are being characterized (IV, CV, TCT).

Here we present the first results of these measurements.

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